

isc Silicon NPN Power Transistors

2SB1261-K

DESCRIPTION

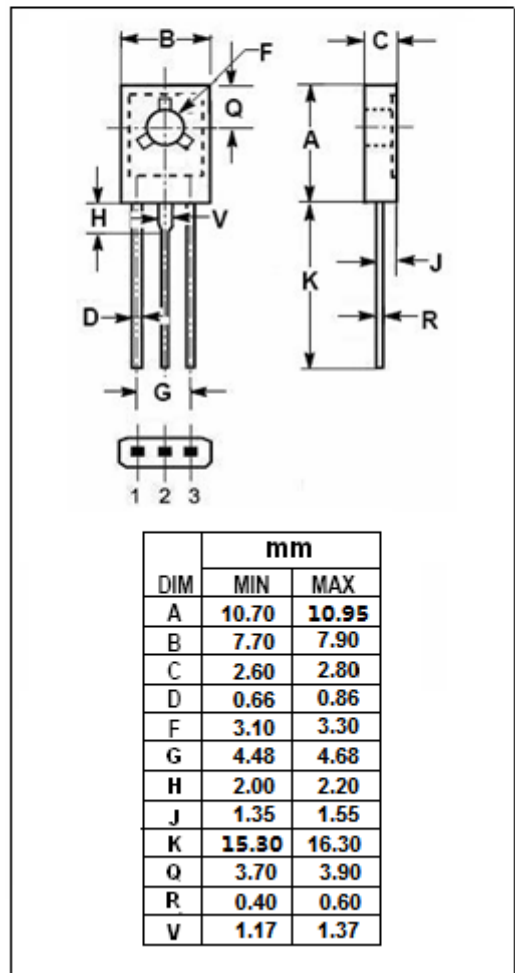
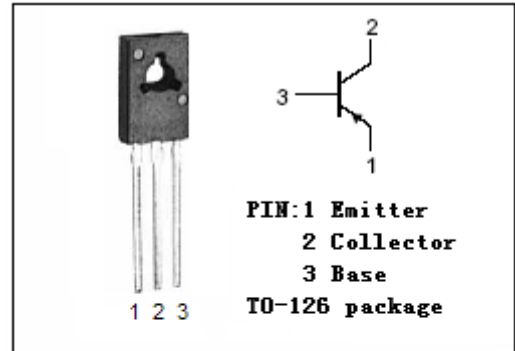
- Low Collector Saturation Voltage
- High Power Dissipation-
: $P_C = 10W(\text{Max}) @ T_C = 25^\circ\text{C}$
- Complement to Type 2SD1899-K

APPLICATIONS

- Designed for use in audio amplifier and switching, especially in hybrid integrated circuits.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	10	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -100μ A; I _E = 0	-60			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; I _B = 0	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -100μ A; I _C = 0	-7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1.5A; I _B = -0.15A			-0.3	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -1.5A; I _B = -0.15A			-1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7V; I _C = 0			-10	μ A
h _{FE1}	DC Current Gain	I _C = -0.2A; V _{CE} = -2V	60			
h _{FE}	DC Current Gain	I _C = -0.6A; V _{CE} = -2V	200		400	
h _{FE}	DC Current Gain	I _C = -2A; V _{CE} = -2V	50			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		40		pF
f _T	Current-Gain—Bandwidth Product	I _E = -1.5A; V _{CE} = -5V		50		MHz